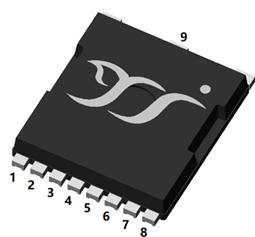
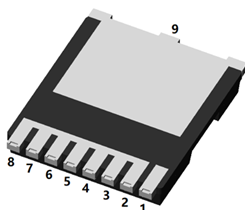


N-Channel Enhancement Mode Field Effect Transistor

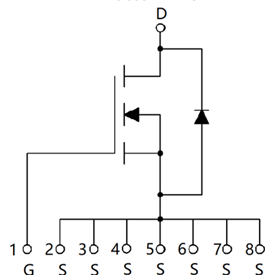


Top View



Bottom View

TOLL



Product Summary

• V_{DS}	100V
• I_D	173A
• $R_{DS(ON)}$ (at $V_{GS}=10V$)	$<3.2m\Omega$
• 100% EAS Tested	
• 100% ∇V_{DS} Tested	
• ESD Level(HBM)	H2

General Description

- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- BMS

Limiting Values

Parameter	Conditions		Symbol	Min	Max	Unit
Drain-source Voltage			V_{DS}	-	100	V
Gate-source Voltage			V_{GS}	-20	20	
Continuous Drain Current (Note 1,2)	Steady-State	$T_A=25^{\circ}\text{C}, V_{GS}=10\text{V}$	I_D	-	22.6	A
		$T_A=100^{\circ}\text{C}, V_{GS}=10\text{V}$		-	14.3	
Continuous Drain Current (Note 1,3)	Steady-State	$T_C=25^{\circ}\text{C}, V_{GS}=10\text{V}, \text{Chip limitation}$		-	173	
		$T_C=100^{\circ}\text{C}, V_{GS}=10\text{V}$		-	109.4	
Pulsed Drain Current	$T_C=25^{\circ}\text{C}, t_p \leq 10\mu\text{s}$		I_{DM}	-	692	
Maximum Body-Diode Continuous Current	$T_C=25^{\circ}\text{C}$		I_S		149	
Avalanche Energy (non-repetitive)	$T_J=25^{\circ}\text{C}, V_G=10\text{V}, R_G=25\Omega, L=1\text{mH}, I_{AS}=31\text{A}$		EAS	-	480.5	mJ
Total Power Dissipation (Note 1,2)	Steady-State	$T_A=25^{\circ}\text{C}$	P_D	-	3	W
		$T_A=100^{\circ}\text{C}$		-	1.2	
Total Power Dissipation (Note 1,3)	Steady-State	$T_C=25^{\circ}\text{C}$		-	178.5	
		$T_C=100^{\circ}\text{C}$		-	71.4	
Junction and Storage Temperature Range			T_J, T_{STG}	-55	150	$^{\circ}\text{C}$

Thermal Resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient (Note 2)	Steady-State	$R_{\theta JA}$	-	41	$^{\circ}C/W$
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	-	0.7	



YJT3D2G10H

■ Electrical Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =1mA, T _J =25°C	100	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =80V, V _{GS} =0V, T _J =25°C	-	-	1	μA
		V _{DS} =80V, V _{GS} =0V, T _J =125°C	-	-	100	
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V, T _J =25°C	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA, T _J =25°C	2.2	2.9	3.7	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =50A, T _J =25°C	-	2.6	3.2	mΩ
Diode Forward Voltage	V _{SD}	I _S =50A, V _{GS} =0V, T _J =25°C	-	0.85	1.2	V
Gate Resistance	R _G	f=1MHz, T _J =25°C	-	1.35	-	Ω
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V, f=1MHz, T _J =25°C	-	3472	-	pF
Output Capacitance	C _{oss}		-	1759	-	
Reverse Transfer Capacitance	C _{rss}		-	60	-	
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =10V, V _{DS} =50V, I _D =50A, T _J =25°C	-	59.4	-	nC
Gate-Source Charge	Q _{gs}		-	16	-	
Gate-Drain Charge	Q _{gd}		-	18	-	
Reverse Recovery Charge	Q _{rr}	I _F =50A, di/dt=100A/μs, V _{GS} =0V, V _R =50V, T _J =25°C	-	46	-	nC
Reverse Recovery Time	t _{rr}		-	44	-	ns
Turn-on Delay Time	t _{D(on)}	V _{GS} =10V, V _{DS} =50V, I _D =50A, R _{GEN} =5Ω, T _J =25°C	-	20	-	ns
Turn-on Rise Time	t _r		-	48	-	
Turn-off Delay Time	t _{D(off)}		-	45	-	
Turn-off Fall Time	t _f		-	34	-	

Note:

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. The value of $R_{\theta JA}$ is measured with the device mounted on the 40mm*40mm*1.1mm single layer FR-4 PCB board with 1 in² pad of 2oz. Copper, in the still air environment with $T_A=25^{\circ}C$. The maximum allowed junction temperature of 150 $^{\circ}C$. The value in any given application depends on the user's specific board design.
3. Thermal resistance from junction to soldering point (on the exposed drain pad).



■ Typical Electrical and Thermal Characteristics Diagrams

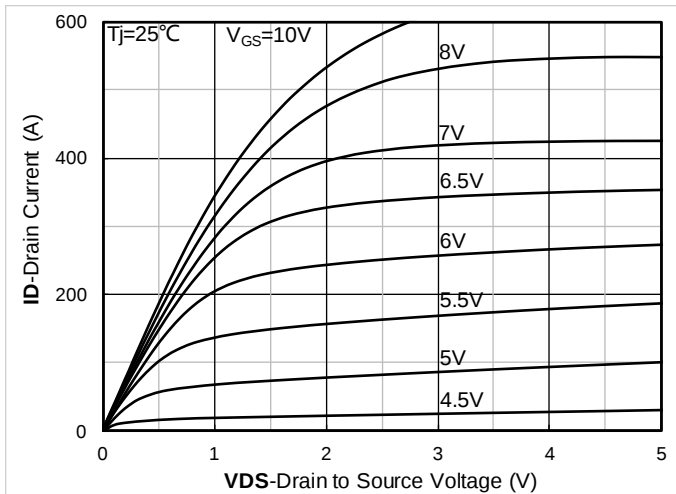


Figure 1. Output Characteristics; typical values

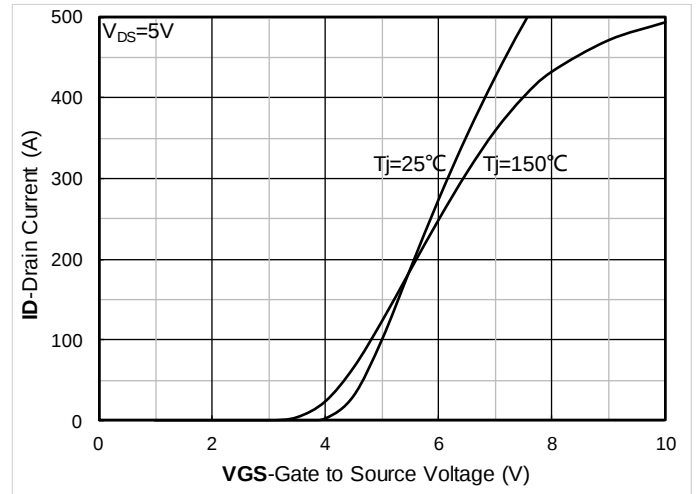


Figure 2. Transfer Characteristics; typical values

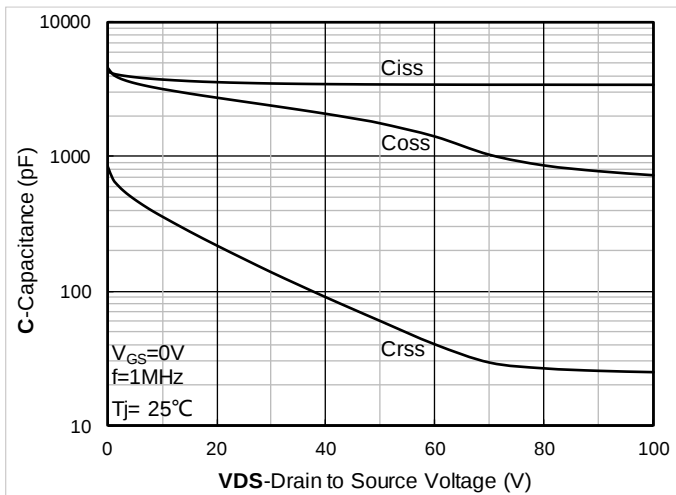


Figure 3. Capacitance Characteristics; typical values

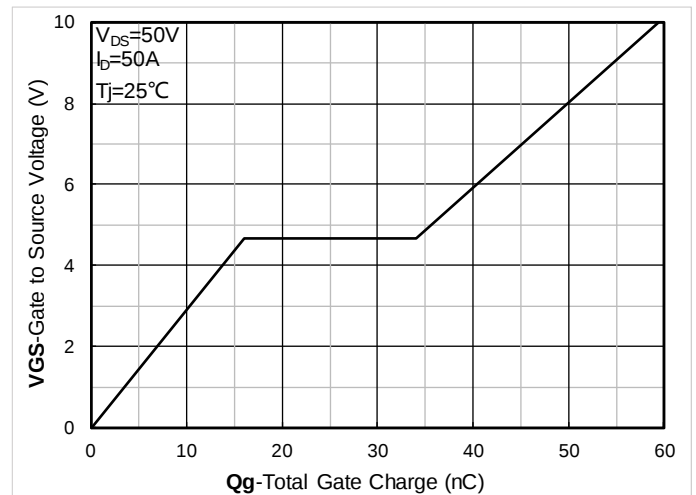


Figure 4. Gate Charge; typical values

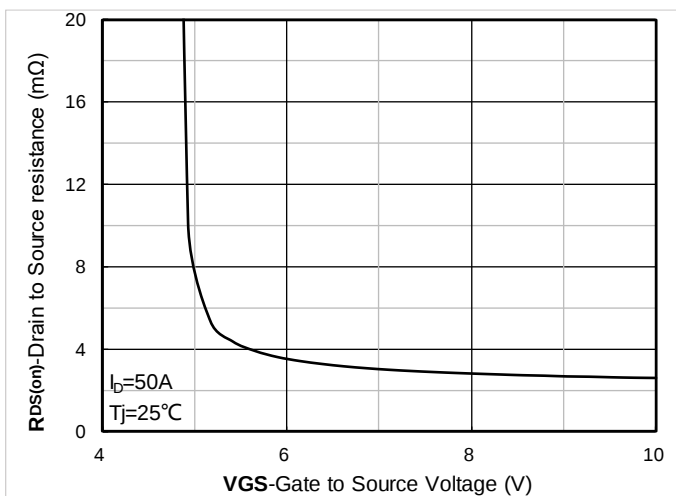


Figure 5. On-Resistance vs. Gate to Source Voltage; typical values

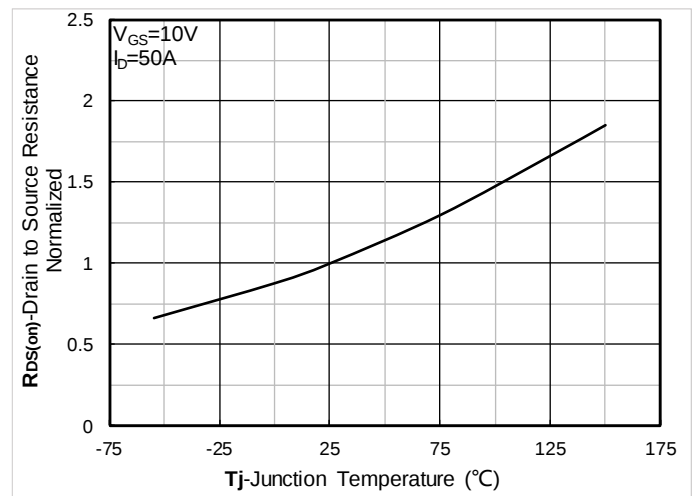


Figure 6. Normalized On-Resistance

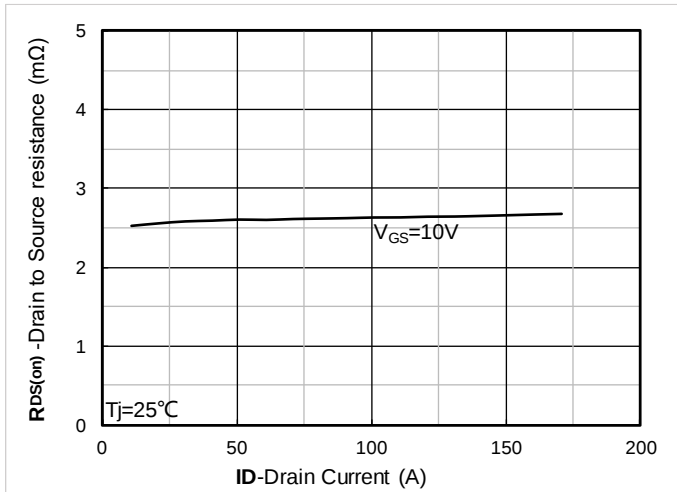


Figure 7. $R_{DS(on)}$ vs. Drain Current; typical values

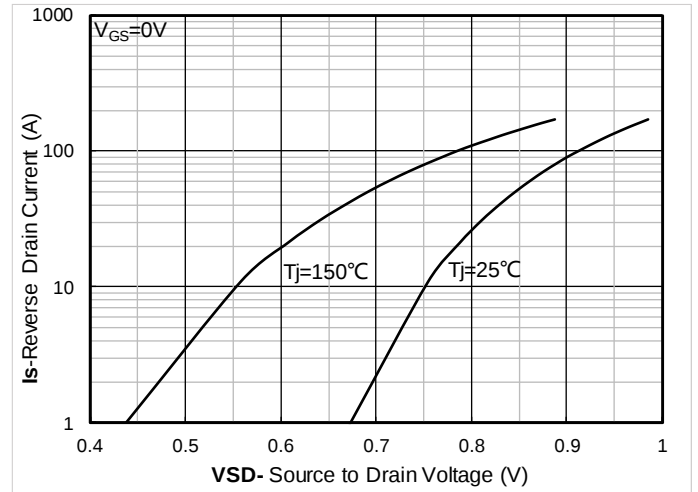


Figure 8. Forward characteristics of reverse diode; typical values

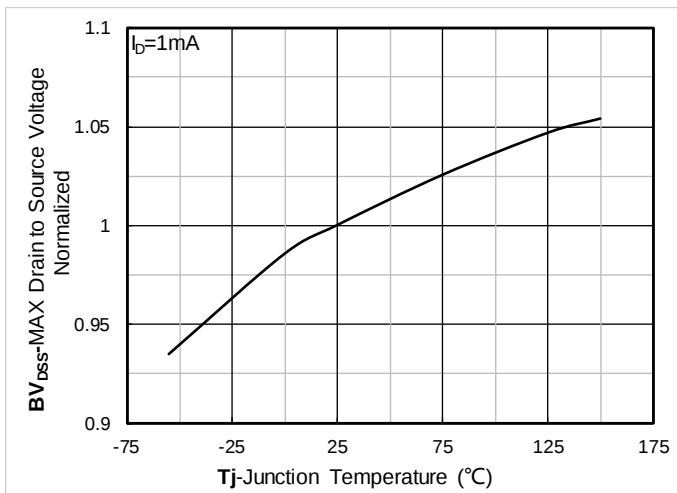


Figure 9. Normalized breakdown voltage

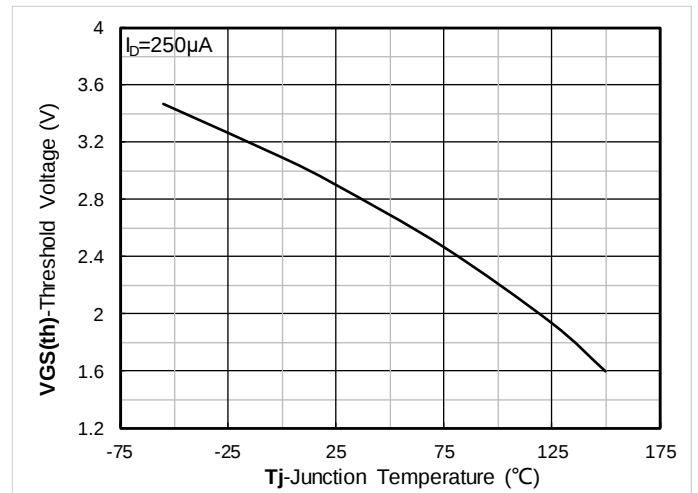


Figure 10. Gate Threshold voltage; typical values

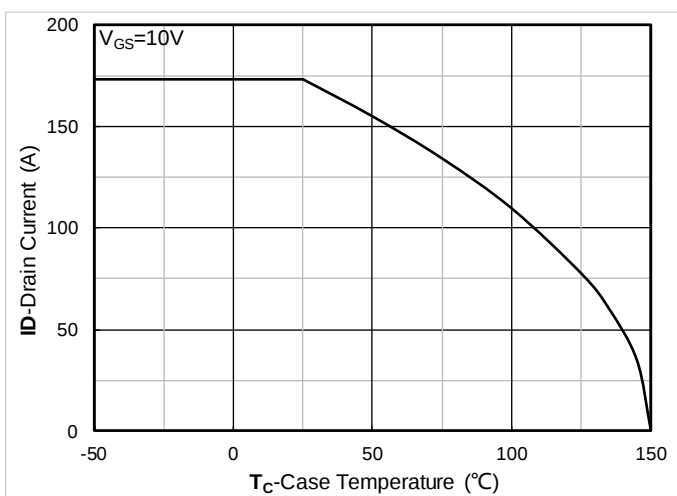


Figure 11. Current dissipation

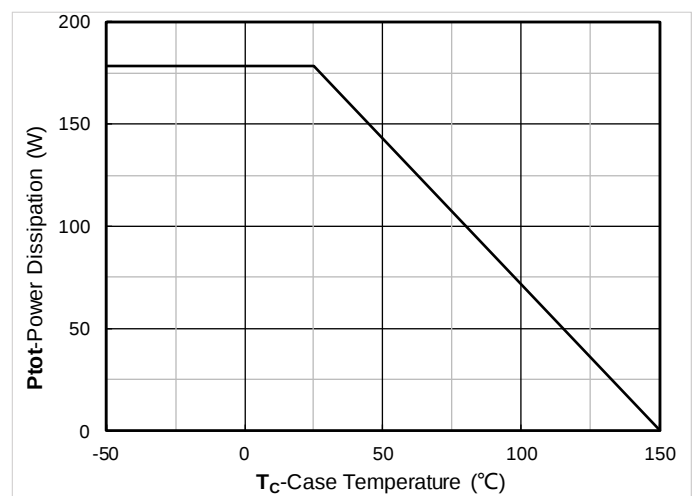


Figure 12. Power dissipation

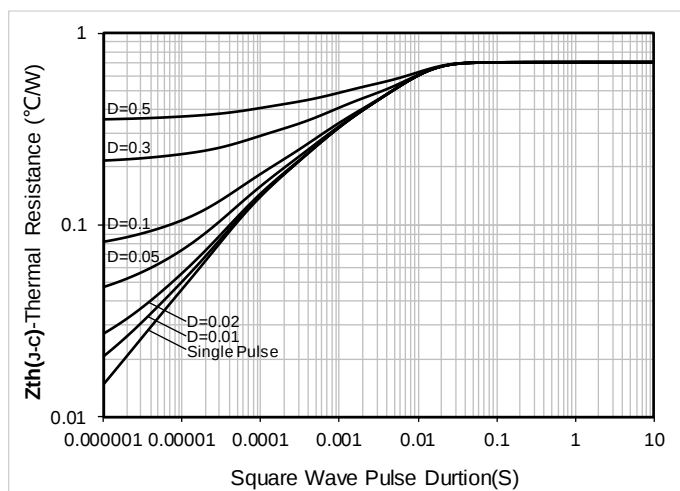


Figure 13. Maximum Transient Thermal Impedance

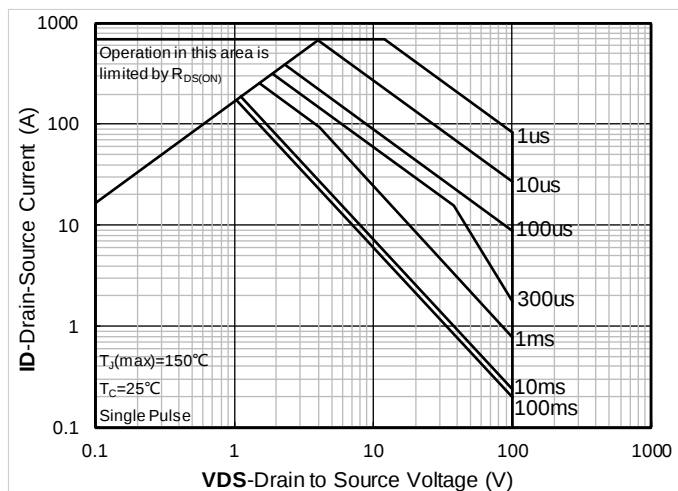


Figure 14. Safe Operation Area

■ Test Circuits & Waveforms

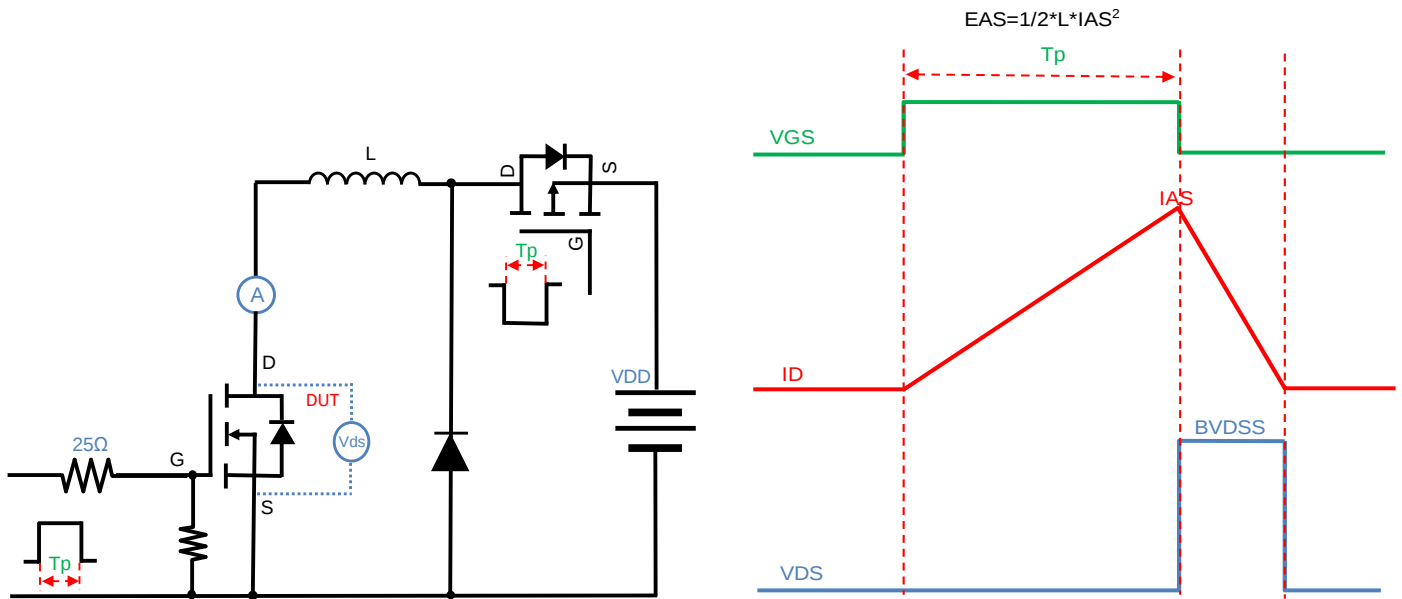


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

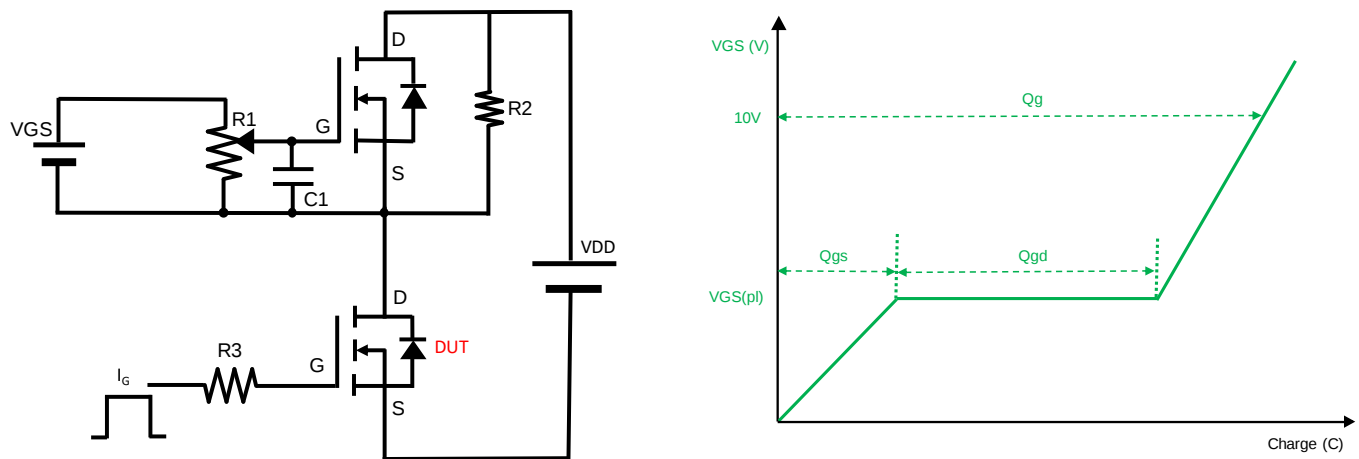


Figure B. Gate Charge Test Circuit & Waveform

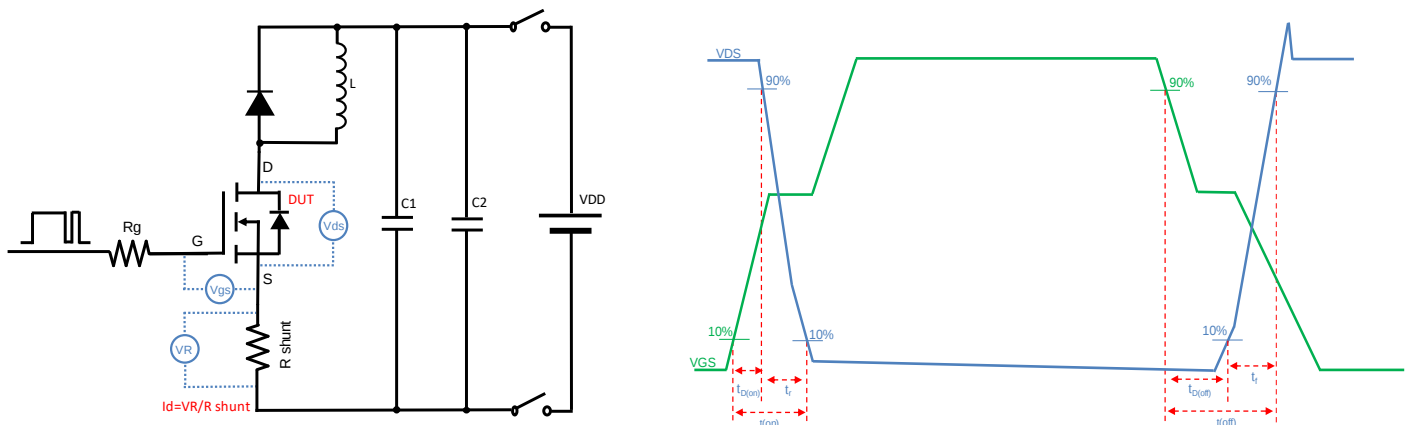


Figure C. Resistive Switching Test Circuit & Waveform

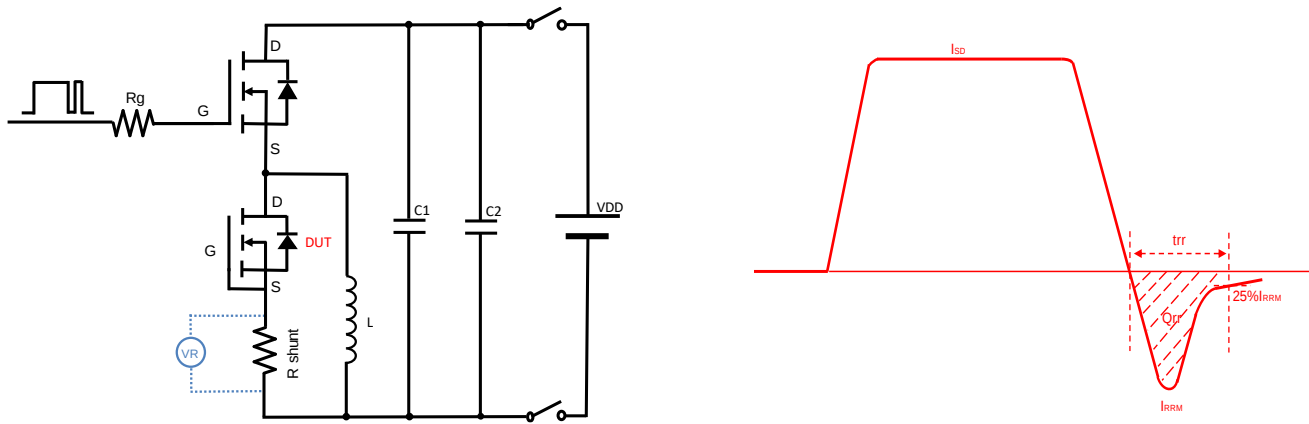
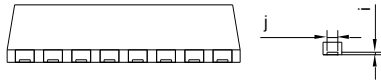
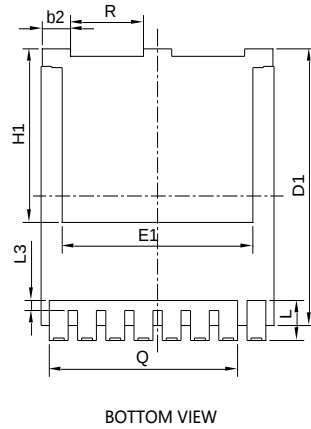
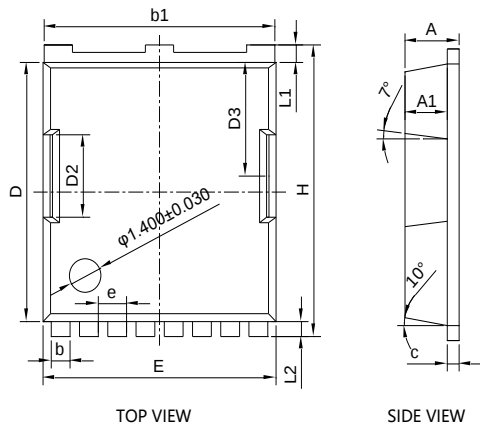


Figure D. Diode Recovery Test Circuit & Waveform



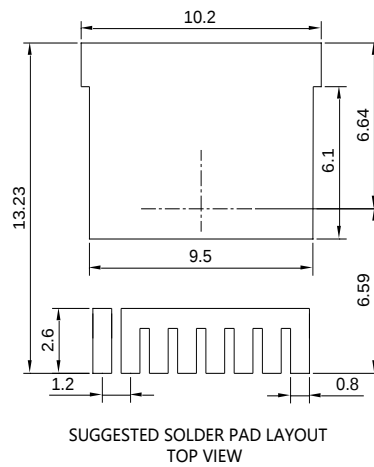
YJT3D2G10H

■ TOLL Package information



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.03\text{mm}$.
3. The pad layout is for reference purposes only.



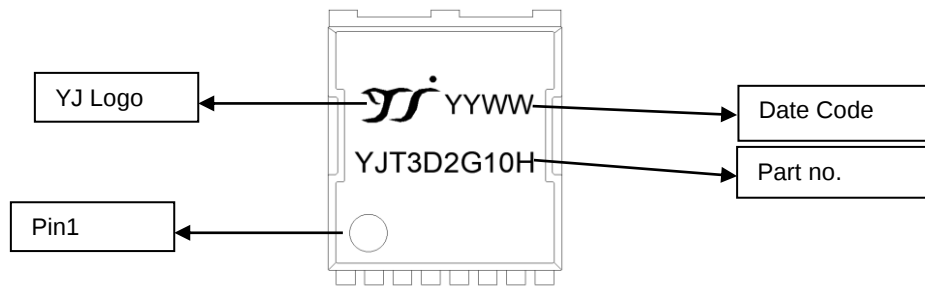
SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	2.2	2.3	2.4
A1	1.7	1.8	1.9
b	0.7	0.8	0.9
b1	9.7	9.8	9.9
b2	1.1	1.2	1.3
c	0.4	0.5	0.6
D	10.28	10.38	10.48
D1	10.98	11.08	11.18
D2	3.2	3.3	3.4
D3	4.45	4.55	4.65
E	9.8	9.9	10
E1	8	8.1	8.2
e	1.2 BSC		
H	11.58	11.68	11.78
H1	6.95 BSC		
i	0.1 REF		
j	0.46 REF		
L	1.5	1.6	1.7
L1	0.6	0.7	0.8
L2	0.5	0.6	0.7
L3	0.3	0.4	0.5
Q	8 REF		
R	3.0	3.1	3.2

UNIT: mm



YJT3D2G10H

■ Marking Information



Note:

1. All marking is at middle of the product body
2. All marking is in laser printing
3. YJT3D2G10H is part no., YYWW is date code, “YY” is year, “WW” is week
4. Body color: Black



Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Yangjie or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

This publication supersedes & replaces all information previously supplied. For additional information, please visit our website <http://www.21yangjie.com> , or consult your nearest Yangjie's sales office for further assistance.